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Surface chemistry of plasma-assisted atomic layer deposition of Al₂O₃ studied by infrared spectroscopy

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The surface groups created during plasma-assisted atomic layer deposition (ALD) of Al₂O₃ were studied by infrared spectroscopy. For temperatures in the range of 25–150 °C, –CH₃ and –OH were unveiled as dominant surface groups after the Al(CH₃)₃ precursor and O₂ plasma half-cycles, respectively. At lower temperatures more –OH and C-related impurities were found to be incorporated in the Al₂O₃ film, but the impurity level could be reduced by prolonging the plasma exposure. The results demonstrate that –OH surface groups rule the surface chemistry of the Al₂O₃ process and likely that of plasma-assisted ALD of metal oxides from organometallic precursors in general. © 2008 American Institute of Physics. [DOI: 10.1063/1.2940598]

Atomic layer deposition (ALD) is the method of choice for the deposition of ultrathin and conformal high-k metal oxide films as required in next-generation memory and transistor devices. To extend the applications of ALD, processes using alternative oxidant sources, such as O₂ and O₃ plasma, are actively researched. Using these oxidant sources, additional reactivity is supplied to the surface chemistry and this potentially allows for deposition at lower temperatures (<150 °C) without compromising film quality.1–3

In order to fully exploit the benefits of the ALD technique, a fundamental understanding of the underlying surface chemistry is of vital importance. To this end the ALD process of Al₂O₃ has been studied in great detail, since it shares generic features to equivalent metal oxide ALD processes. The conventional, thermal ALD process of Al₂O₃ using Al(CH₃)₃ precursor and H₂O was found to be ruled by the formation of –CH₃ and –OH surface groups after the precursor and oxidant half-cycles, respectively, with the formation of volatile CH₄ in both half-reactions.4–6 In the O₃-based ALD process, the formation of –CH₃ surface groups, and volatile CH₄ after Al(CH₃)₃ adsorption were found to be similar to the H₂O-based process. During the O₃ half-cycle, however, the formation of CH₄ and C₂H₄ have been reported1,2 and it is still debated whether –OH or formate [–O(OH)]CH groups are the dominant surface species produced by the O₃ reactions.2,7 In our previous work on plasma-assisted ALD of Al₂O₃, we observed the formation of CH₄ after Al(CH₃)₃ adsorption, while mainly CO, CO₂, and H₂O were formed in the O₂ plasma half-cycle through combustionlike surface reactions.5,8 The surface chemistry during this plasma-assisted ALD process could not be fully resolved yet, because no measurements on the surface groups were available.

Despite the different oxidant sources employed, it is intriguing to note that the dependence of growth per cycle on the deposition temperature is quite similar for the different oxidant sources for ALD of Al₂O₃, as shown in Fig. 1 for H₂O,9–13 O₃,2,13 and O₂ plasma.9 For temperatures >100 °C, the growth per cycle of Al₂O₃ monotonically decreases with increasing deposition temperature for all three oxidant sources and the differences are relatively small. Only below 100 °C, the growth per cycle significantly differs which has been attributed to difficulties to achieve saturation when dosing H₂O.9,10 For the H₂O-based process, the decrease in growth per cycle with increasing temperature has been related to the thermal stability of the –OH surface groups which are involved in the Al(CH₃)₃ chemisorption reactions.5,10 The O₂ plasma-based process shows a similar decrease but for the complete temperature range (25–400 °C). This resemblance might indicate some similarities between the surface groups involved in plasma-assisted and thermal ALD of Al₂O₃. To better understand the dependence of the growth per cycle on the deposition temperature, however, insight into the surface chemistry of plasma-assisted ALD of Al₂O₃ is necessary.

The primary objective of this letter is to elucidate the surface chemistry of plasma-assisted ALD of Al₂O₃ through detection of the surface groups generated in the half-cycles by means of transmission infrared spectroscopy measurements. The main result of this study is the observation that –CH₃ and –OH surface groups are predominantly formed after the Al(CH₃)₃ and O₂ plasma half-cycles, respectively.

FIG. 1. (Color online) Literature data on the growth per cycle of Al₂O₃ as a function of deposition temperature for ALD processes using Al(CH₃)₃ as precursor and H₂O, O₃, or O₂ plasma as oxidant source. The data presented were corrected for differences in mass density and represent the growth per cycle of a film with a mass density of 3.0 g cm⁻³ as typically reported for ALD Al₂O₃ films.

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This observation implies that –OH surface groups rule the surface chemistry during plasma-assisted ALD of Al₂O₃, similar to the H₂O-based process. Also the influence of the deposition temperature (25–150 °C), the incorporation of impurities, and a direct comparison with the thermal ALD process at 150 °C are addressed. The results will facilitate the design of improved low temperature (<150 °C) ALD processes and it is expected that they have generic implications for plasma-assisted ALD processes of other metal oxide films.

Plasma-assisted and thermal ALD processes of Al₂O₃ were studied in a wall-heated reactor equipped with an O₂-operated inductively coupled plasma source and bubblers with Al(CH₃)₃ (99.9999%, Akzo Nobel) and H₂O (Ultra-pur®, >99.9999%, Merck). The cycles consisted typically of 25 ms of Al(CH₃)₃ dosing followed by 2 s O₂ plasma exposure or 2×240 ms H₂O dosing in the plasma-assisted and thermal ALD process, respectively. The Al₂O₃ films were deposited onto KBr flats that also served as infrared viewports in the reactor. It was verified that the growth per cycle and Al₂O₃ film quality were similar to results obtained on substrates positioned on the substrate holder. In between the ALD half-reactions, transmission infrared spectra (2 ×256 scans) were collected by an infrared interferometer (Bruker, Tensor 27) with an external liquid-N₂ cooled HgCdTe detector (Bruker, D313). The absorbance spectra were averaged over 40 ALD cycles to reduce the noise level to ~5 ×10⁻⁶.

The surface species created during the plasma-assisted ALD half-cycles of Al₂O₃ were studied at a deposition temperature of 150 °C and were directly compared to the results of the thermal ALD process carried out at the same temperature. From qualitative comparison of the differential vibrational spectra shown in Fig. 2(a), it is clear that the same types of surface species are created in both ALD processes. After the Al(CH₃)₃ precursor adsorption, –CH₃ surface groups appear as observed in stretching (asymmetric ~2937 cm⁻¹, symmetric ~2896 cm⁻¹, and bending overtone ~2831 cm⁻¹), deformation (~1208 cm⁻¹), and rocking (~750 cm⁻¹) modes, while –OH surface groups disappear as observed in the broad stretching (3750–2770 cm⁻¹) mode. This broad –OH stretching feature originates from various types of –OH groups on the Al₂O₃ surface, ranging from unassociated –OH (3800–3700 cm⁻¹) to associated –OH (3700–2700 cm⁻¹) modes. For both ALD processes, the differential spectra clearly show that –OH surface groups are created after the reaction of the O₂ plasma and the H₂O oxidant with the –CH₃ surface groups.

For the O₂ plasma-based process, the influence of deposition temperature on the surface groups was studied for films deposited at 25, 100, and 150 °C, as shown in Fig. 2(b). From the similarities in the differential vibrational spectra, it is concluded that the surface chemistry at lower temperatures also proceeds predominantly via the formation of –CH₃ and –OH surface species. At lower temperatures, the amount of –OH surface groups created by the O₂ plasma strongly increased and a broadening of the –OH stretching modes was observed. The broadening at lower deposition temperatures can be attributed to the dipole interaction (in particular, hydrogen bonding) between the densely packed –OH surface groups. Moreover, the presence of physisorbed H₂O on the Al₂O₃ surface can also be of influence.

In addition, an unassigned broad feature around ~900 cm⁻¹ is observed for the films deposited by plasma-assisted ALD. The feature is most likely not related to the broad Al–O phonon mode (~954 cm⁻¹ in Ref. 15), since its magnitude increased with increasing temperature opposite to the trend observed for the growth per cycle of the Al₂O₃ films (Fig. 1).

Insight into the type and absolute amount of impurities incorporated into the Al₂O₃ films can be deduced from a differential spectrum obtained after a full ALD cycle (i.e., basically adding the differential spectra for the two half-cycles). From such differential spectra, it is concluded that –OH groups were incorporated in the Al₂O₃ bulk with the amount of –OH incorporated increasing when going to lower deposition temperatures. This observation is in line with previous reports, as well as with the compositional data of Al₂O₃ films deposited in the temperature range studied, i.e., x=[O]/[Al]=1.6 with ~4 at. % H at 150 °C, x=1.7 with ~7 at. % H at 100 °C, and x=2.1 with ~15 at. % H at 25 °C (all using 2 s O₂ plasma exposure). From the spectra, no evidence is found for the incorporation of –CH₃ groups into the bulk Al₂O₃ film at the studied temperatures. Interestingly for the film deposited at 25 °C, carbon-related impurities (1662 cm⁻¹ after the O₂ plasma step, which changed into a broad feature (1600–1450 cm⁻¹) after the Al(CH₃)₃ dosing. The peaks observed can be attributed to impurities containing C=O or COO bonds indicating incomplete removal of the carbon from the surface during the 2 s O₂ plasma step at 25 °C. The incorporation of these surface features into the Al₂O₃ bulk after Al(CH₃)₃ precursor adsorption is expected to account for the shift and broadenings of the ~900 cm⁻¹ feature.
the O$_2$ plasma species. Therefore the following surface reactions are proposed for plasma-assisted ALD of Al$_2$O$_3$:

$$\text{AlOH}^+ + \text{Al(CH}_3)_3(g) \rightarrow \text{AlOAl(CH}_3)_2^+ + \text{CH}_4(g), \quad (1)$$

$$\text{AlCH}_3_3 + 4\text{O}_2(g) \rightarrow \text{AlOH}^+ + \text{CO}_2(g) + \text{H}_2\text{O}(g), \quad (2)$$

where the asterisks designate the surface species and only the case of monofunctional adsorption is considered for simplicity. Moreover, the amount of –OH groups involved in the surface reactions increased for lower deposition temperatures which can be related to the higher growth per cycle at these temperatures. It was also demonstrated that the high reactivity delivered by the O$_2$ plasma allows for film deposition at temperatures down to room temperature, but under these conditions a longer plasma exposure time was required to complete the surface reactions and reduce the impurity content of the Al$_2$O$_3$ films. Tuning the plasma reactivity in the ALD process is thus key in obtaining high quality films at low deposition temperatures. Because combustionlike reactions of organic surface ligands by O$_2$ plasma species have been reported for more plasma-assisted ALD processes, it is expected that the surface chemistry discussed is generic for plasma-assisted ALD processes of high-$\kappa$ metal oxides using (similar) metal-organic precursors and O$_2$ plasma.

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